

BACK-END

MOS-FET

IGBT

SWITCHING TIME TEST SYSTEM スイッチングタイムテストシステム

SWS1240ZZF

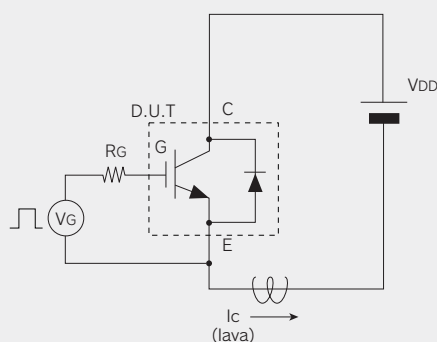
1200V
1200A4000A
(Short Circuit)

NEW



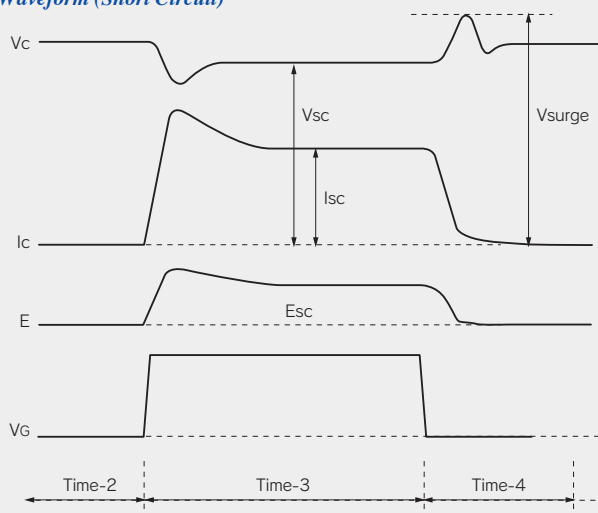
- SWS1240ZZF has been designed to test switching characteristics and energy tolerance at short circuit that are by IGBT inductive load. This model can test 6 devices at maximum.
- IGBTの誘導負荷によるスイッチング特性および短絡時におけるエネルギー耐量を試験するシステムです。最大6素子までの測定を可能としています。

Fundamental Test Circuit (Short Circuit)



Ic current is controlled by VG voltage.
Ic電流値はVG電圧で制御

Measurement Waveform (Short Circuit)



MODEL	SWS1240ZZF	
TEST ITEMS		
L-LOAD SWITCHING	Ic(I _D), td(on), tr, td(off), tf, e(on), e(off)	
SHORT CIRCUIT ASO	V _{sc} , I _{sc} , V _{surge} , E _{sc}	
SETTING RANGE		
MEASURABLE DEVICE	MOS-FET, IGBT	
MEASUREMENT RANGE	1ns~99.9μs	
VDD	30V~1200V	1V STEP
VGF/VGR	0.1V~±30.0V	0.1V STEP
Time-1	0.5μs~999.9μs	
Time-2	0.5μs~99.9μs	
Time-3	0.5μs~999.9μs	
Time-4	0.5μs~99.9μs	
Time-5	0.5μs~999.9μs	
SW I _D (Limit)	20A~1200A	10A STEP
ASO I _D (Limit)	20A~4000A	10A STEP
V _D (Limit)	10V~1200V	1V STEP
DETECT DELAY	0.1μs~999.9μs	0.1μs STEP
BINNING		
OPEN/SHORT CHECK	VGF ON : V _{CE} >V _{DD} ×10%...OPEN VGF OFF : V _{CE} <V _{DD} ×90%...SHORT	
BIN INDICATION	PASS, LIMIT-FAIL, OPEN, SHORT	
DIMENSIONS & WEIGHT		
UNIT-A	550(W)×880(D)×1700(H)…230kg	
UNIT-B	550(W)×1200(D)×1700(H)…260kg	
JIG ADAPTER	410(W)×510(D)×123(H)…225kg	